Variation of Superconducting Transition Temperature in Hole-Doped Copper-Oxides

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The experimentally observed difference of superconducting critical temperature T_c in hole-doped cuprates is studied by using an extended interlayer coupling model for layered d-wave superconductors. We show that the change of the maximum T_c from series to series is determined by the next nearest neighboring hopping t', while the difference of the maximum T_c among the compounds in a homogeneous series is controlled by the interlayer pairing strength. Our results provide helpful guidelines in the search for new high-T_c superconductors.

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The nature of high temperature superconductors is a challenge problem in condensed matter physics. A common feature of copper oxide superconductors is the presence of CuO_2 plane. It has been observed that the superconducting critical temperature T_c varies parabolically with the hole concentration n_H in CuO_2 plane with a maximum T_c^{max} at an optimal doping level [1, 2]. However, T_c^{max} attainable is different from series to series, e.g: 35 K in $La_{2-x}Sr_xCuO_4$ [3] and 97 K in $HgBa_2CuO_{4+}$ [4]. An obvious question is what is the crucial parameter that governs the T_c^{max} of each family.

Among various parameters proposed, the Madelung potential at the apical oxygen relative to that at the planar oxygens [5] was found to correlate with T_c^{max} rather well, pointing to the primary importance of the apical oxygens for the electronic structure relevant to superconductivity. Further investigations [6, 7] revealed that the effect of the apical oxygens on high-T_c superconductivity in reality translates into a correlation between T_c^{max} and the next nearest neighbor hopping parameter t' in the t-t'-J model. In these approaches, t' was considered as a single parameter reflecting the main difference among various cuprates. If we consider the homologous series, the universality of such a correlation would be seriously questioned. For example, the bilayer and trilayer Tl-based and Hg-based compounds have almost same t' [7], but their T_c^{max}'s are significantly different.

Our goal in this work is to extract and identify which parameters govern the T_c behaviors in hole-doped cuprates. We apply an interlayer coupling model to CuO_2 layer systems and then calculate T_c based on the BCS gap equation with d-wave symmetry. Our results suggest that the difference of T_c^{max} from series to series is the result of different next nearest neighbor hopping t', while the difference of T_c^{max} between the compounds in a homologous series is controlled by the interlayer coupling strength T_J.

The effective layered Hamiltonian we consider is

$$H = \sum_{lk} (\varepsilon_k - \mu) c^{\dagger}_{lk} c_{lk} - \sum_{lkk'} V_{kk'} c^{\dagger}_{k\uparrow} c^{\dagger}_{l\,-k\downarrow} c_{l\,-k'\downarrow} c_{k'\uparrow} + \sum_{\langle ll' \rangle k} T_J(k) c^{\dagger}_{k\uparrow} c^{\dagger}_{l\,-k\downarrow} c_{l'\,-k\downarrow} c_{k\uparrow} \quad ; \qquad (1)$$

where ε_k is the quasiparticle dispersion, μ is the chemical potential, $c^{\dagger}_{lk}$ is a quasiparticle creation operator pertaining to the layer (l) with two-dimensional wave-vector k and spin σ. The summation over ll' runs over the layer indices of the unit cell. The intralayer interaction $V_{kk'}$ is assumed to be independent of l. The interlayer tunneling is parameterized by $T_J(k) = T_J(\cos k_x - \cos k_y)^4$ [8].

We assume that the superconducting gap is characterized by the nonvanishing order parameter $b^l_k = \langle c^l_{k\uparrow} c^l_{-k\downarrow} \rangle$. Based on the BCS theory the gap function Δ^l_k satisfies the following equation

$$\Delta^l_k = \sum_{k'} V_{kk'} b^l_{k'} + T_J(k)(b^{l+1}_k + b^{l-1}_k) \quad ; \qquad (2)$$

where $b^l_k = \Delta^l_k \chi^l_k$ and the generalized pair susceptibility is $\chi^l_k = (2E^l_k)^{-1} \tanh(\beta E^l_k/2)$. The quasiparticle spectrum is $E^l_k = \sqrt{(\varepsilon_k - \mu)^2 + |\Delta^l_k|^2}$.

The spatial dependence of the gap is taken the form [9]: $\Delta^l_k = \Delta_k e^{i\phi l}$. Then the general solution of the homogeneous part is

$$\Delta^l_k = \Delta^+_k e^{i\phi l} + \Delta^-_k e^{-i\phi l} \quad . \qquad (3)$$

Considering the fact that the gap vanishes on the layer ends $l = 0$ and $n+1$, the natural boundary conditions for the gap are $\Delta^0_k = \Delta^{n+1}_k = 0$. The wave vector of the oscillating gap is then determined by

$$\begin{vmatrix} 1 & 1 \\ e^{i\phi} & e^{-i\phi} \end{vmatrix} \begin{vmatrix} \Delta^+_k \\ \Delta^-_k \end{vmatrix} = 0 \quad .$$

The vanishing determinant of the matrix provides a nontrivial solution only when $\phi = \pi/(n+1)$ where ϕ is an

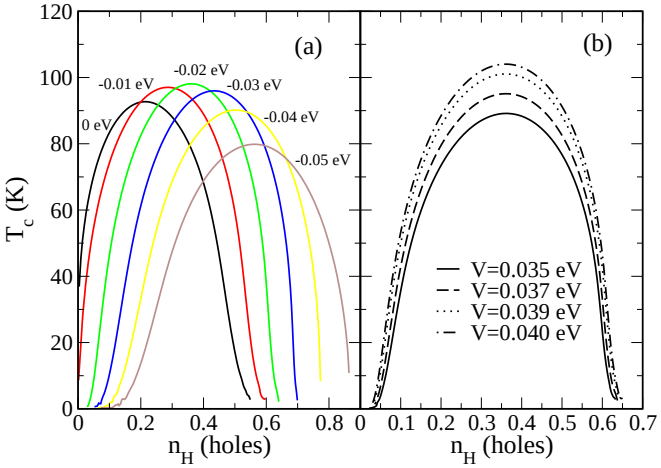

FIG. 1: T_c vs n_H for various t^0 with $V = 0.038$ eV (a) and for various V with $t^0 = -0.02$ eV (b) in monolayer cuprates.

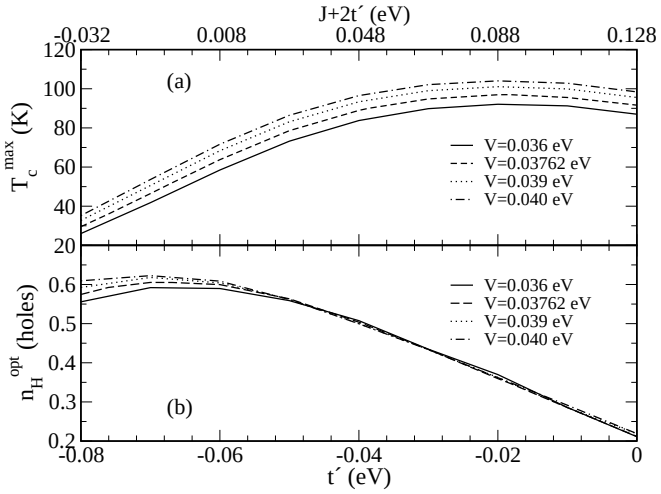

FIG. 2: Calculated T_c^{max} (a) and n_H^{opt} (b) as a function of t^0 (or $J + 2t^0$) for various V in monolayer cuprates.

integer. Thus we obtain $_k^+ = -_k$ $_k$. The solution of spatial dependence of the gap is then

$$_k^1 = 2i\ _k \sin\frac{m}{n+1} \quad : \tag{4}$$

The solution with the lowest energy is nodeless inside the CuO_2 layers which leads to $m = 1$ for the superconducting state.

Around critical temperature T_c, we can take $_k^1$ in a simple form: $_k^1 \simeq (2E_k)^{-1}\tanh(E_k/2)$ $_k$ with $E_k = \sqrt{(\varepsilon_k -)^2 + |_k|^2}$. Then gap magnitude $_k$ can be written as

$$-_k \sum_{k^0} V_{kk^0}\ _{k^0}\tanh(E_{k^0}/2)/2E_{k^0} = f(n)T_J(k)\ _k\ ; \tag{5}$$

where $f(n) = 2\cos(/(n+1))$.

To account for the experimental observed d-wave gap, we assume a d-wave pairing potential

$$V_{kk^0} = V g(k)g(k^0)\ ;\ g(k) = \cos k_x - \cos k_y\ ; \tag{6}$$

The gap magnitude is thus $_k = {}_0 g(k)$ and the parameter $_0$ is determined by the following self-consistent equation:

$$1 = \frac{1}{2N}\sum_k \frac{V g^2(k) + f(n)T_J(k)}{E_k}\tanh\left(\frac{E_k}{2}\right) \quad : \tag{7}$$

The value of T_c in layered d-wave superconductors is then obtained by solving Eq. (7) at $_0 = 0$.

In order to self-consistently calculate T_c for a given in conjunction with the equation determining n_H, we need an explicit form of ε_k. It has been established [10] that the quasiparticle excitation spectrum of cuprates can be well described by the t-t^0-J model. Within the framework of the t-t^0-J model, the dispersion ε_k is given by [11, 12]

$$\varepsilon_k = (J + 2t^0)\cos k_x \cos k_y + \frac{J}{4}(\cos 2k_x + \cos 2k_y) \quad : \tag{8}$$

For monolayer insulator La_2CuO_4, experiments [13] and theoretical calculations [14] give a $J = 0.128$ eV. There are small variations of J among various Cu-O insulators [15] but we expect a value of $J = 0.128$ eV is a generally good representation for all Cu-O materials. Then one can determine T_c as a function of n_H based on Eqs. (7) and (8) once having knowledge of t^0, V, or/and T_J.

First we consider the variation of T_c in monolayer ($n = 1$) hole-doped cuprates. Figures 1 (a) and (b) show the calculated T_c in monolayer superconductors as a function of n_H in some interested parameters range of t^0 and V. As shown, T_c initially increases with increasing n_H, takes a maximum around an optimal doping level n_H^{opt} and then decreases with further increasing n_H. This parabolic relation between T_c and n_H agrees with general experimental observations in monolayer cuprates [1, 2]. We notice that T_c^{max} systematically changes with t^0, but it monotonically increases with V, as one expects. The difference between these two parameters is that n_H^{opt} depends significantly on t^0, while it scarcely changes for different values of V. These results indicate that the parameters controlling T_c^{max} would be either t^0 or V or both of them.

In Fig. 2 we plotted the t^0 dependence of both T_c^{max} and n_H^{opt} for monolayer cuprates. As t^0 increases, T_c^{max} increases and then decreases through a maximum for all V studied. The occurrence of the maximum implies that the enhancement of T_c^{max} due to the increase in t^0 is limited. n_H^{opt} behaves in a similar manner with t^0 as T_c^{max}. For $J + 2t^0 > 0$, n_H^{opt} decreases with increasing t^0. Al-

TABLE I: Summary of the experimental results of the critical temperature T_c^{max} at optimal doping, the distance $d_{Cu\ O(a)}$ between the copper and apical oxygen atoms, the distance $d_{Cu\ O(p)}$ between the copper and in-plane oxygen atoms, and the calculated values of the bond valence sums of copper V_{Cu} and the difference in the Madelung site potentials V_M for a hole between the in-plane oxygen and copper atoms in some typical monolayer cuprates.

Cuprates	T_c^{max} (K)	$d_{Cu\ O(a)}$ (Å)	$d_{Cu\ O(p)}$ (Å)	V_{Cu}	V_M (eV)
$La_{1.85}Sr_{0.15}CuO_4$	35	2.4124	1.8896	2.539	49.620
$Bi_2Sr_{1.61}La_{0.39}CuO_{6+}$	36	2.461	1.901	2.437	48.437
$TlBa_{1.2}La_{1.8}CuO_5$	52	2.500	1.9240	2.280	48.409
$Tl_2Ba_2CuO_6$	90	2.714	1.9330	2.135	47.081
$HgBa_2CuO_{4+}$	97	2.780	1.9375	2.091	46.81

TABLE II: The critical temperature T_c^{max} and the ratio of T_J/V in homogeneous copper-oxides series at optimal doping. The brackets are the experimental data taken from the works of Refs. [2, 3, 4, 5, 16, 17, 23, 25, 28].

n	1	2	3	4	5	1	T_J/V
$Bi_2Sr_2Ca_{n-1}Cu_nO_{2n+4+}$	36.0 (36)	90.0 (90)	115.5 (110)	127.8	134.7	150.7	0.1945
$Tl_2Ba_2Ca_{n-1}Cu_nO_{2n+4+}$	90.0 (90)	115.0 (115)	125.2 (125)	130.1 (116)	132.9	139.4	0.0906
$TlBa_2Ca_{n-1}Cu_nO_{2n+3+}$	52.0 (52)	107.0 (107)	131.3 (133.5)	143.0 (127)	149.5	164.6	0.1930
$HgBa_2Ca_{n-1}Cu_nO_{2n+2+}$	97.0 (97)	127.0 (127)	139.2 (135)	145.2 (129)	148.6 (110)	156.4	0.1135

though T_c^{max} depends on V, n_H^{opt} is nearly independent of V over a wide range of t^0.

To trace the clue to the change of T_c^{max} among monolayer cuprates, we list in Table I the experimental results of T_c^{max} [2, 3, 4, 16, 17], the distance $d_{Cu\ O(a)}$ between the copper and apical oxygen atoms and the distance $d_{Cu\ O(p)}$ between the copper and in-plane oxygen atoms taken from the works in Refs. [4, 5], the calculated values of bond valence sums (BVS) of copper V_{Cu} and the difference in the Madelung site potential for a hole between the copper and the in-plane oxygen V_M. To get effective BVS of copper, we follow the method proposed by Brown [18]. The results of V_M based on the structural data are taken from the works in Refs. [5, 19]. Here we observe one important experimental fact: T_c^{max} increases systematically with enlarging $d_{Cu\ O(a)}$. Band structure calculations [7] revealed that t^0 increases with $d_{Cu\ O(a)}$ for the monolayer cuprates reported so far. Thus the increase of T_c^{max} with increasing t^0 should capture the basic physics of the monolayer cuprates.

It has been proposed [20, 21] that V_{Cu} and V_M are two essential factors governing T_c and represent an essentially equivalent physical content. Materials with larger T_c^{max} tend to have a smaller V_{Cu} [20] or V_M [21]. Since the variation of V_{Cu} or V_M reflects the corresponding change of n_H [21, 22, 23], the increase of the calculated T_c^{max} with decreasing n_H^{opt} for a wide t^0 range is obviously consistent with the experimental data shown in Table I. This n_H^{opt} dependence of T_c^{max} is also consistent with the muon spin resonance (μSR) measurements [24]. On the other hand, the fact that the change of T_c^{max} with V is almost independent of n_H^{opt} (Fig. 2(b)) rules out the possibility of V being a dominant factor in governing the change in T_c^{max}. The present results lead us to conclude that the increase of T_c^{max} with $d_{Cu\ O(a)}$ among the monolayer cuprates is a result of the increase in t^0. One prediction is that T_c^{max} decreases with further increasing t^0 after through a saturation. Thus, materials with a relatively long $d_{Cu\ O(a)}$ bondlength would not expect to have a high T_c^{max}.

The values of t^0 were determined in a self-consistent way as follows. From Fig. 2 (a) we learned that there exists a maximum for given V. Among the monolayer cuprates discovered so far, $HgBa_2CuO_{4+}$ possesses the highest T_c^{max} of 97 K. Assuming this is the highest value in all monolayer cuprates, we derived a value of $V = 0.3762$eV from curves of T_c^{max} versus t^0. Equation (7) yields $t^0 = -0.0183$ eV for the optimally doped $HgBa_2CuO_{4+}$. For other optimally doped monolayer compounds with $T_c^{max} < 97$K, t^0 should be smaller than -0.0183 eV because of their shorter $d_{Cu\ O(a)}$. The relative t^0 is then obtained by using the experimentally observed T_c^{max}.

Next we consider n, the number of CuO_2 layers, dependence of T_c in the layered homogeneous series. In general, T_c^{max} initially increases with n, maximizes at $n = 3$, and then decreases with further increasing n [25]. To calculate T_c for multilayers, we use the same dispersion ε_k and V as obtained from the monolayer. The interlayer tunneling strength T_J is determined by using the experimental values of T_c^{max} for monolayer and bilayer compounds in the same homogeneous series. As an example, in Fig. 3, we show curves of calculated T_c versus n_H as a function of layer number n in the Hg-based

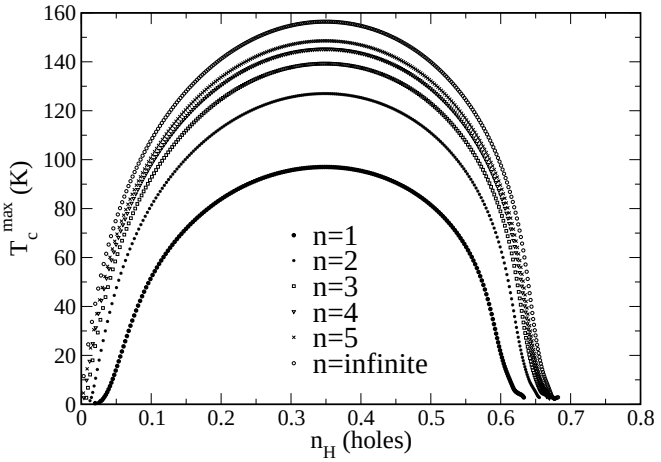

FIG. 3: Calculated T_c vs n_H in $HgBa_2Ca_{n-1}Cu_nO_{2n+2+}$ as a function of the number of CuO_2 layers.

series. The parabolic behavior is generally observed for any layered compound. The calculated T_c^{max} in four typical homogeneous series are summarized in Table II. The experimental results are also listed for comparison. As can be seen, T_c^{max} initially increases with increasing n and then saturates as $n \to 1$. This behavior is in good agreement with those obtained from both the interlayer mechanism [9, 26] and Ginzburg-Landau theory [27, 28]. The upper limit of T_c^{max} for infinite layer compound is in the range of 139.4 to 164.6 K. The highest T_c^{max} of 164.6 K is found in the Tl-based series. Our results for $n = 3$ agree with experiments very well. The predictions made here for T_c^{max} of the trilayer compound is the best ones compared to previous theories [9, 26, 27, 28].

The present study shows that interlayer coupling is the driving force for the enhancement of T_c^{max} for multilayer systems. This does not conflict with the experimental fact that T_c^{max} saturates as $n \geq 3$. In fact, there exist five-fold (outer) and four-fold CuO_2 (inner) planes surrounded by pyramidal and square oxygens in the multilayer system. Investigations carried out by different experimental techniques and model calculations [23, 29, 30, 31] showed that the distribution of charge carriers are nonhomogeneous among the CuO_2 sheets and the hole concentration in the outer CuO_2 plane is larger than that in the inner CuO_2 plane. BVS analyses [23] and NMR studies [31] on the Hg-based series revealed that the highest T_c^{max} corresponds to the smallest difference in n_H between two types of CuO_2 planes. When the number of CuO_2 layer is larger than three, the reduction of T_c^{max} comes from the large difference in n_H between the outer and inner CuO_2 planes. For compounds with more than three CuO_2 planes, the enhancement of T_c^{max} seems possible at ambient pressure if one can adequately dope the inner planes.

In summary, we have investigated the observed T_c variation in hole-doped cuprates on the basis of an extended interlayer coupling model. We demonstrate that the next nearest neighboring hopping t' dominates the variation of the maximum T_c from series to series and the interlayer coupling strength controls the difference of the maximum T_c among the compounds in a layered homogeneous series. These results provide helpful guidelines in the search for new high-T_c superconductors.

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